



PATENT ABSTRACTS OF JAPAN

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(54) RESIST PATTERN FORMING METHOD

(57) Abstract:

PURPOSE: To provide a resist pattern forming method with which the thinning of top film by the effect of defocus and the roundness of bottom part can be eliminated simultaneously by a method wherein the resists having a different solubility are formed in a multilayer structure such as a two-layer structure, for example, when a developing operation is conducted after exposing treatment.

CONSTITUTION: The resist pattern forming method used in the photolithography process for manufacture of a semiconductor device, includes the steps of forming a photoresist film in a multilayer structure consisting of a lower layer resist thin film 11 and an upper layer resist thin film 12 having different solubilities when de-

veloping after exposing treatment, and effecting exposure for formation of a circuit pattern on the multilayer photoresist film. The photoresist film of multilayer structure is developed in such a manner that the photoresist thin film 12, to be formed as the upper layer, has a solubility at developing lower than that of the photoresist film 11 of the lower layer for the same exposure.

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